National Semiconductor

74LCX00
Low Voltage Quad 2-Input NAND Gate with 5V Tolerant Inputs

General Description

The LCX00 contains four 2-input NAND gates. The inputs tolerate voltages up to 7V allowing the interface of 5V systems to 3V systems.

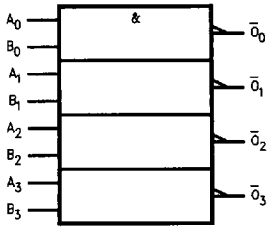
The 74LCX00 is fabricated with advanced CMOS technology to achieve high speed operation while maintaining CMOS low power dissipation.

Features

- 5V tolerant inputs
- 5.2 ns t_{PD} max, 10 μA I_{CCQ} max
- Power down high impedance inputs and outputs
- Supports live insertion/withdrawal
- 2.0V–3.6V V_{CC} supply operation
- ±24 mA output drive
- Implements patented Quiet Series™ noise/EMI reduction circuitry
- Functionally compatible with 74 series 00
- Latch-up performance exceeds 500 mA
- ESD performance:
  Human body model > 2000V
  Machine model > 200V

Logic Symbol

IEEE/IEC



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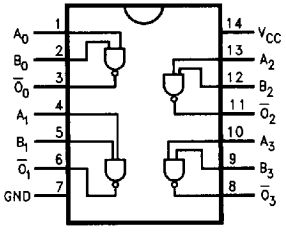
Connection Diagram

Pin Assignment for SOIC and TSSOP



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Pin Names	Description
A_n, B_n	Inputs
$\overline{O}_n$	Outputs

	SOIC JEDEC	SOIC EIAJ	TSSOP
Order Number	74LCX00M 74LCX00MX	74LCX00SJ 74LCX00SJX	74LCX00MTC 74LCX00MTCX
See NS Package Number	M14A	M14D	MTC14

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Symbol	Parameter	Value	Conditions	Units
V_{CC}	Supply Voltage	−0.5 to +7.0		V
V_I	DC Input Voltage	−0.5 to +7.0		V
V_O	DC Output Voltage	−0.5 to V_{CC} + 0.5	Output in High or Low State (Note 2)	V
I_{IK}	DC Input Diode Current	−50	V_I < GND	mA
I_{OK}	DC Output Diode Current	−50 +50	V_O < GND V_O > V_{CC}	mA
I_O	DC Output Source/Sink Current	±50		mA
I_{CC}	DC Supply Current per Supply Pin	±100		mA
I_{GND}	DC Ground Current per Ground Pin	±100		mA
T_{STG}	Storage Temperature	−65 to +150		°C

Note 1: The Absolute Maximum Ratings are those values beyond which the safety of the device cannot be guaranteed. The device should not be operated at these limits. The parametric values defined in the "Electrical Characteristics" table are not guaranteed at the Absolute Maximum Ratings. The "Recommended Operating Conditions" table will define the conditions for actual device operation.

Note 2: I_O Absolute Maximum Rating must be observed.

Recommended Operating Conditions

Symbol	Parameter		Min	Max	Units
V_{CC}	Supply Voltage	Operating Data Retention	2.0 1.5	3.6 3.6	V
V_I	Input Voltage		0	5.5	V
V_O	Output Voltage	HIGH or LOW State	0	V_{CC}	V
I_{OH}/I_{OL}	Output Current	V_{CC} = 3.0V − 3.6V V_{CC} = 2.7V		±24 ±12	mA
T_A	Free-Air Operating Temperature		−40	85	°C
$\Delta t/\Delta V$	Input Edge Rate, V_{IN} = 0.8V–2.0V, V_{CC} = 3.0V		0	10	ns/V

DC Electrical Characteristics

Symbol	Parameter	Conditions	V_{CC} (V)	T_A = −40°C to +85°C		Units
				Min	Max	
V_{IH}	HIGH Level Input Voltage		2.7–3.6	2.0		V
V_{IL}	LOW Level Input Voltage		2.7–3.6		0.8	V
V_{OH}	HIGH Level Output Voltage	I_{OH} = −100 μA	2.7–3.6	V_{CC} − 0.2		V
		I_{OH} = −12 mA	2.7	2.2		V
		I_{OH} = −18 mA	3.0	2.4		V
		I_{OH} = −24 mA	3.0	2.2		V
V_{OL}	LOW Level Output Voltage	I_{OL} = 100 μA	2.7–3.6		0.2	V
		I_{OL} = 12 mA	2.7		0.4	V
		I_{OL} = 16 mA	3.0		0.4	V
		I_{OL} = 24 mA	3.0		0.55	V
I_I	Input Leakage Current	0 ≤ V_I ≤ 5.5V	2.7–3.6		±5.0	μA
I_{OFF}	Power-Off Leakage Current	V_I or V_O = 5.5V	0		10	μA
I_{CC}	Quiescent Supply Current	V_I = V_{CC} or GND	2.7–3.6		10	μA
		3.6V ≤ V_I, V_O ≤ 5.5V	2.7–3.6		±10	μA
ΔI_{CC}	Increase in I_{CC} per Input	V_{IH} = V_{CC} −0.6V	2.7–3.6		500	μA

AC Electrical Characteristics (Preliminary)

Symbol	Parameter	$T_A = -40°C$ to $+85°C$				Units
		$V_{CC} = 3.3V \pm 0.3V$		$V_{CC} = 2.7V$		
		Min	Max	Min	Max	
t_{PHL} t_{PLH}	Propagation Delay	1.5 1.5	5.2 5.2	1.5 1.5	6.0 6.0	ns
t_{OSHL} t_{OSLH}	Output to Output Skew (Note 3)		1.0 1.0			ns

Note 3: Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH to LOW (t_{OSHL}) or LOW to HIGH (t_{OSLH}).

Dynamic Switching Characteristics

Symbol	Parameter	Conditions	V_{CC} (V)	$T_A = 25°C$ Typical	Unit
V_{OLP}	Quiet Output Dynamic Peak V_{OL}	$C_L = 50$ pF, $V_{IH} = 3.3V$, $V_{IL} = 0V$	3.3	0.8	V
V_{OLV}	Quiet Output Dynamic Valley V_{OL}	$C_L = 50$ pF, $V_{IH} = 3.3V$, $V_{IL} = 0V$	3.3	0.8	V

Capacitance

Symbol	Parameter	Conditions	Typical	Units
C_{IN}	Input Capacitance	V_{CC} = Open, $V_I = 0V$ or V_{CC}	7	pF
C_{OUT}	Output Capacitance	$V_{CC} = 3.3V$, $V_I = 0V$ or V_{CC}	8	pF
C_{PD}	Power Dissipation Capacitance	$V_{CC} = 3.3V$, $V_I = 0V$ or V_{CC}, F = 10 MHz	25	pF